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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/667,871	09/22/2003	Yee-Chia Yeo	TSM03-0553	1170
43859 75	590 10/21/2005		EXAMINER KENNEDY, JENNIFER M	
	IATSIL, L.L.P.			
17950 PRESTON ROAD, SUITE 1000 DALLAS, TX 75252			ART UNIT .	PAPER NUMBER
Dilbbito, 171	, 5252		2812	

DATE MAILED: 10/21/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

<u> </u>			A.H
<u> </u>	Application No.	Applicant(s)	
Advisory Action	10/667,871	YEO ET AL.	
Before the Filing of an Appeal Brief	Examiner	Art Unit	
	Jennifer M. Kennedy	2812	
The MAILING DATE of this communication app	ears on the cover sheet with the	correspondence add	ress
The MAILING DATE of this communication app.  THE REPLY FILED 10 October 2005 FAILS TO PLACE THIS  1. ☑ The reply was filed after a final rejection, but prior to orchis application, applicant must timely file one of the foll places the application in condition for allowance; (2) a N (3) a Request for Continued Examination (RCE) in comfollowing time periods:  a) ☑ The period for reply expires 3 months from the mailing date of this Adevent, however, will the statutory period for reply expire later the Examiner Note: If box 1 is checked, check either box (a) or (b MONTHS OF THE FINAL REJECTION. See MPEP 706.07 (Extensions of time may be obtained under 37 CFR 1.136(a). The date or been filed is the date for purposes of determining the period of extension CFR 1.17(a) is calculated from: (1) the expiration date of the shortened shove, if checked. Any reply received by the Office later than three montice arened patent term adjustment. See 37 CFR 1.704(b).  NOTICE OF APPEAL  2. ☐ The Notice of Appeal was filed on A brief in comfof filing the Notice of Appeal has been filed, any reply must AMENDMENTS  3. ☐ The proposed amendment(s) filed after a final rejection (a) ☐ They raise new issues that would require further complete the proposed amendment (s) filed after a final rejection (b) ☐ They are not deemed to place the application in beappeal; and/or (d) ☐ They present additional claims without canceling a NOTE: (See 37 CFR 1.116 and 41.33(a)).  4. ☐ The amendments are not in compliance with 37 CFR 1. Applicant's reply has overcome the following rejection (c) ☐ Newly proposed or amended claim(s) would be rejected is proposed and summer and the new or amended claim(s) would be rejected in the non-allowable claim(s) is (or will be) as follows: Claim(s) withdrawn from consideration: Claim(s) withdrawn from consideration: Claim(s) withdrawn from consideration:	Examiner  Jennifer M. Kennedy  ears on the cover sheet with the APPLICATION IN CONDITION For the same day as filing a Notice owing replies: (1) an amendment, Notice of Appeal (with appeal fee) in pliance with 37 CFR 1.114. The report the final rejection.  Wisory Action, or (2) the date set forth in the han SIX MONTHS from the mailing date of the final rejection.  In which the petition under 37 CFR 1.136 and the corresponding amount of the fee tatutory period for reply originally set in the safter the mailing date of the final rejection.  In pliance with 37 CFR 41.37 must be extension thereof (37 CFR 41.37 (e. be filed within the time period set in the safter the mailing date of filing a brid onsideration and/or search (see Noow); extern form for appeal by materially a corresponding number of finally reports to the date of filing a brid onsideration and/or search (see Noow); extern form for appeal by materially a corresponding number of finally reports of the date of filing a brid onsideration and/or search (see Noow); extern form for appeal by materially a corresponding number of finally reports of the date of filing a provided below or appended.  Discriptions and sufficient reasons why the afficient reasons why the afficient of the date of filing a provided below or appended.	Art Unit 2812  correspondence add OR ALLOWANCE. of Appeal. To avoid al affidavit, or other evid in compliance with 37 (or other final rejection, whichever of the final rejection. FIRST REPLY WAS FILE (a) and the appropriate extension of the final Office action; or (2) (a) the appropriate extension of the final Office action; or (2) (b) (c) (c) (c) (c) (c) (c) (c) (c) (c) (c	pandonment of ence, which CFR 41.31; or none of the er is later. In no D WITHIN TWO ension fee have on fee under 37 as set forth in (b) by reduce any this of the date of the appeal. a).  because  If the issues for explanation of explanation of explanation of explanation of explanation of will not be entered is necessary will not be ils to provide a 1).
REQUEST FOR RECONSIDERATION/OTHER	on of the status of the claims after	entry is below or attac	nea.
11.  The request for reconsideration has been considered b See Continuation Sheet.			nce because:
<ul><li>12. ☑ Note the attached Information Disclosure Statement(s)</li><li>13. ☐ Other:</li></ul>	. (PTO/SB/08 or PTO-1449) Рареі	Jennifer M. Kenned Primary Examiner Art Unit: 2812	Innedy

Continuation of 11. does NOT place the application in condition for allowance because: Applicant's arguments are not persuasive. Applicant argues the combination of Nowak et al. and Yu et al. stating that Nowak et al. teaches away from using a high k dielectric. Applicant refers examiner to citations throughout Nowak et al. to support the position that Nowak et al. teaches away form using a high-k dielectric. Nowak et al. teaches that low parasitic capacitance is desired. The examiner points out that there is a distinction between parasitic capacitance (leakage) and capacitance. Parasitic capacitance or leakage current is unwanted current as understood by Applicant (see instant specification at [0005] and [0026]-[0028]). The combined reference Yu et al. teaches that the high-k dielectric reduces leakage current (see column 2, lines 1-5), and allows for thicker dielectric layers to be formed whereby both greater capacitance and device speed are obtained with less gate-to-channel leakage current (see column 2, lines 23-30). Thus, the high k dielectric of Yu et al. is also concerned with reducing the parasitic capacitance or leakage current and is combinable with Nowak et al.